

Ultra Fast Recovery Rectifier Diodes

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- * High Surge Capacity
- * Low Power Loss, High efficiency
- * Glass Passivated chip junctions
- * 150 °C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- * Low Forward Voltage , High Current Capability
- * High-Switching Speed 35 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

MAXIMUM RATINGS

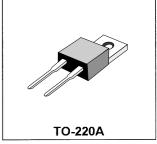
Characteristic	Symbol	U10A				Unit
		05	10	15	20	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	150	200	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	105	140	V
Average Rectifier Forward Current	I _{F(AV)}	10			Α	
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware,single phase,60Hz)	FSM	200			A	
Operating and Storage Junction Temperature Range	T _j , T _{stg}	- 65 to + 150			°C	

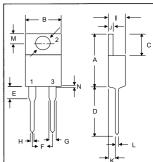
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	U10A				Unit
		05	10	15	20	1
Maximum Instantaneous Forward Voltage $(I_F = 10 \text{ Amp}, T_C = 25 ^{\circ}\text{C})$ $(I_F = 10 \text{ Amp}, T_C = 100 ^{\circ}\text{C})$	V _F	0.975 0.890			V	
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_c = 25$ °C) (Rated DC Voltage, $T_c = 100$ °C)	I _R			0 00	-	uA
Reverse Recovery Time ($I_F = 0.5 \text{ A}$, $I_R = 1.0 \text{ A}$, $I_{rr} = 0.25 \text{ A}$)	T _{rr}	35		ns		
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P	C _P 120			pF	

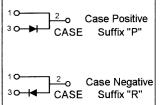
ULTRA FAST RECTIFIERS

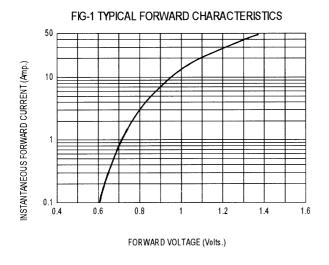
10 AMPERES 50 -- 200 VOLTS

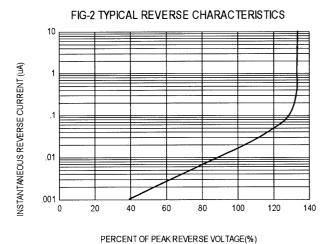


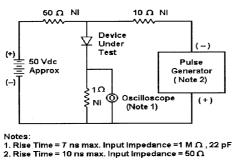


DIM	MILLMETERS			
	MIN	MAX		
Α	14.68	15.32		
В	9.78	10.42		
С	6.01	6.52		
D [']	13.06	14.62		
E	3.57	4.07		
F	4.83	5.33		
G	1.12	1.36		
Н	0.72	0.96		
1	4.22	4.98		
J	1.14	1.36		
K	2.20	2.97		
L	0.33	0.55		
M	2.48	2.98		
N		1.00		
0	3.70	3.90		

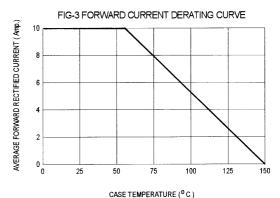


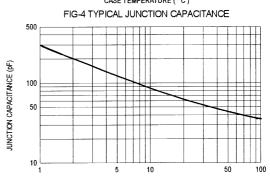


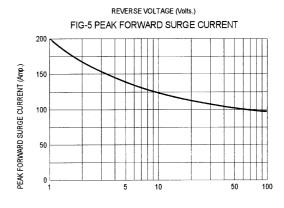


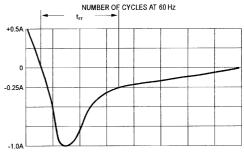












Set time base for 10 ns/div

Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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